



A Product Line of Diodes Incorporated



FCX458

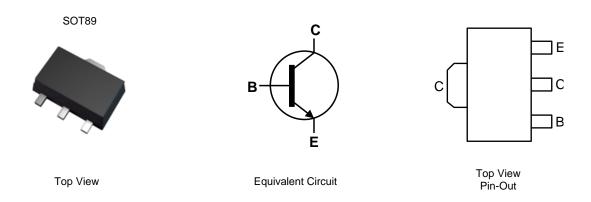
400V NPN HIGH VOLTAGE TRANSISTOR IN SOT89

Features

- BV_{CEO} > 400V
- I_C = 225mA Continuous Collector Current
- I_{CM} = 500mA Peak Pulse Current
- Excellent h_{FE} Characteristics up to 100mA
- Low saturation voltage V_{CE(sat)} < 200mV @ 20mA
- Complementary PNP Type: FCX558
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.055 grams (Approximate)



Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FCX458TA	AEC-Q101	N58	7	12mm	1,000

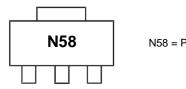
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.

3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



N58 = Product Type Marking Code





Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	400	V
Collector-Emitter Voltage	V _{CEO}	400	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	lc	225	mA
Peak Pulse Current	I _{CM}	500	mA
Base Current	IB	200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		0.7		
Dower Discinction	(Note 6)	P _D	1.0	W	
Power Dissipation	(Note 7)		1.5		
	(Note 8)		2.0		
	(Note 5)	R _{0JA}	178		
	(Note 6)		125		
Thermal Resistance, Junction to Ambient Air	(Note 7)		83	°C/W	
	(Note 8)		60		
Thermal Resistance, Junction to Lead	(Note 9)	R _{θJL}	22]	
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C		

ESD Ratings (Note 10)

Notes:

				- 1
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

5. For a device mounted with the exposed collector pad on minimum recommended pad layout (MRP) 1oz copper that is on a single-sided

1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

6. Same as Note 5, except the device is mounted with the exposed collector pad on 15mm x 15mm 1oz copper.

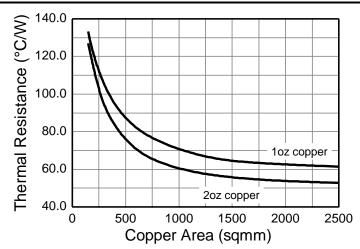
7. Same as Note 5, except the device is mounted with the exposed collector pad on 25mm x 25mm 1oz copper.

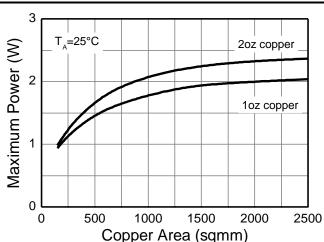
8. Same as Note 5, except the device is mounted with the exposed collector pad on 50mm x 50mm 1oz copper.

9. Thermal resistance from junction to solder-point (on the exposed collector pad).

10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

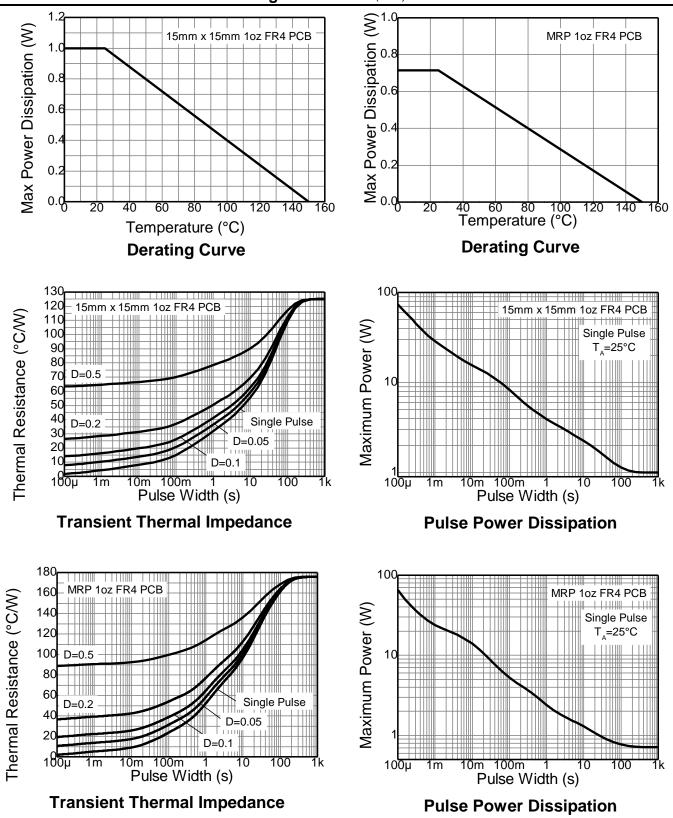








Thermal Characteristics and Derating Information (cont.)







Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

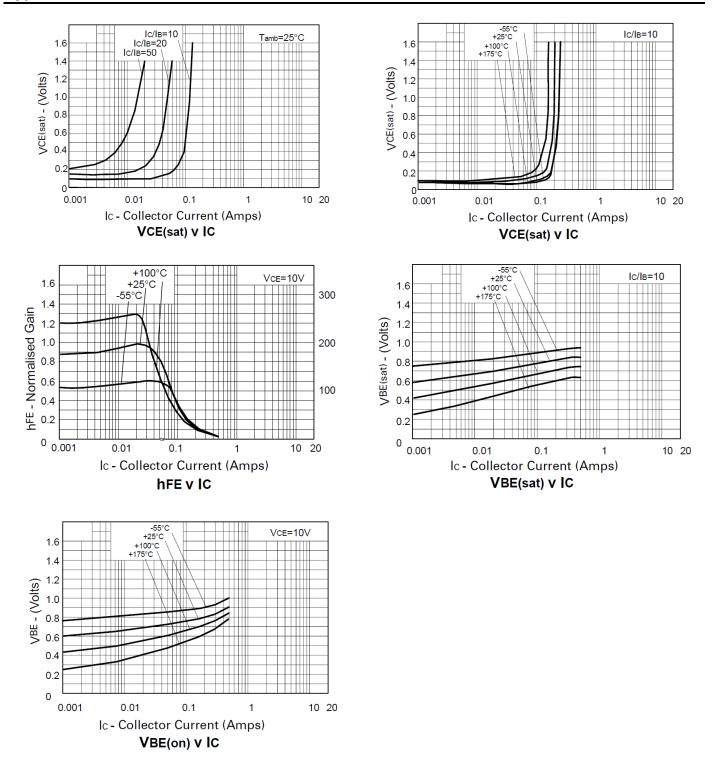
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	400	_	_	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	400	_	—	V	I _C = 1mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	_	—	V	I _E = 100μA
Collector-Base Cutoff Current	I _{CBO}	—	<1	100	nA	V _{CB} = 320V
Collector Cutoff Current	ICES	—	<1	100	nA	V _{CES} = 320V
Emitter Cutoff Current	I _{EBO}	—	<1	100	nA	$V_{EB} = 5.6V$
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}	_	_	200 500	mV	$I_{C} = 20$ mA, $I_{B} = 2$ mA $I_{C} = 50$ mA, $I_{B} = 6$ mA
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	—	_	900	mV	$I_{C} = 50 \text{mA}, I_{B} = 5 \text{mA}$
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(on)}	—	—	900	mV	$I_{C} = 50 \text{mA}, V_{CE} = 10 \text{V}$
DC Current Gain (Note 11)	hfe	100 100 15	_	300	_	$I_{C} = 1mA, V_{CE} = 10V$ $I_{C} = 50mA, V_{CE} = 10V$ $I_{C} = 100mA, V_{CE} = 10V$
Transitional Frequency	f⊤	50	_	_	MHz	$I_C = 10$ mA, $V_{CE} = 20$ V, f = 20MHz
Output Capacitance	C _{obo}	—	—	5	pF	V _{CB} = 20V. f = 1MHz
Turn-On Time	t _{on}	—	135	—	ns	I _C =50mA, V _{CE} =100V,
Turn-Off Time	t _{off}	_	2260	_	ns	$I_{B1} = 5mA, I_{B2} = -10mA$

Note: 11. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%





Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

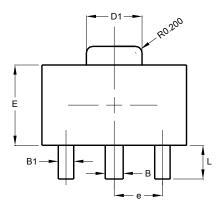


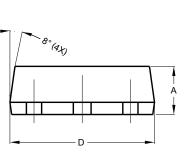


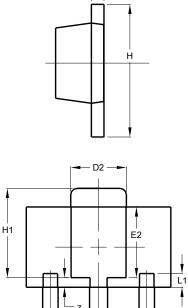


Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.





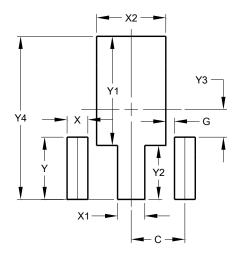


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SOT89						
Dim	Min	Max	Тур			
Α	1.40	1.60	1.50			
В	0.50	0.62	0.56			
B1	0.42	0.54	0.48			
c	0.35	0.43	0.38			
D	4.40	4.60	4.50			
D1	1.62	1.83	1.733			
D2	1.61	1.81	1.71			
Е	2.40	2.60	2.50			
E2	2.05	2.35	2.20			
е	-	-	1.50			
Н	3.95	4.25	4.10			
H1	2.63	2.93	2.78			
L	0.90	1.20	1.05			
L1	0.427 REF					
Z	0.30 REF					
All	All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value
Dimensions	(in mm)
С	1.500
G	0.244
Х	0.580
X1	0.760
X2	1.933
Y	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530

For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking. Note:





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